

IN THE CLAIMS:

1-9. (Previously Withdrawn)

10. (Currently Amended) A semiconductor laser device comprising:
an etching control layer, which is formed on a first region of a compound semiconductor substrate and has a composition different from a composition of the substrate;
a first semiconductor laser structure, which is defined over the etching control layer and which is made up of a first multiple semiconductor layers including a first active layer with a composition different from that of the etching control layer; and
a second semiconductor laser structure, which is defined on a second region of the substrate and which is made up of a second multiple semiconductor layers including a second active layer,
wherein no part of the etching control layer exists between the second region of the substrate and the second semiconductor laser structure,
wherein the first multiple semiconductor layers are made of III-V compound, ~~said the~~ the V element is one selected from the group consisting of As and P,
wherein the second multiple semiconductor layers are made of III-V compound, the V element is another selected from the group consisting of As and P, and
wherein the etching control layer has a V element different from the V element comprising of the first multiple semiconductor layers.
~~wherein the composition of the etching control layer is different from the composition of the first multiple semiconductor layers.~~

11. (Previously Canceled)

12. (Previously Presented) A semiconductor laser device according to Claim 10, wherein the etching control layer has a thickness of more than 0 μ m and equal to or less than 0.1 μ m.

13. (Previously Presented) A semiconductor laser device according to Claim 10, further comprising a buffer layer between the etching control layer, formed on the first region of the substrate, and the first semiconductor laser structure.

14. (Currently Amended) A semiconductor laser device according to Claim 13, wherein the etching control layer is formed out of a ~~Group~~ Group III-V compound semiconductor layer containing P, and

wherein the buffer layer is formed out of a GaAs layer.

15. (Currently Amended) A semiconductor laser device according to Claim 10, wherein the compound semiconductor substrate is a GaAs substrate, and

wherein the etching control layer is formed out of a ~~Group~~ Group III-V compound semiconductor layer containing P.

16. (Previously Amended) A semiconductor laser device according to Claim 10, wherein the etching control layer is made of $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ (where $0 \leq x \leq 1$ and $0 \leq y \leq 1$), and

wherein the first semiconductor laser structure includes semiconductor layers made of $\text{Al}_z\text{Ga}_{1-z}\text{As}$ (where $0 \leq z \leq 1$).

17. (Previously Amended) A semiconductor laser device according to Claim 10, wherein the etching control layer is made of $\text{Al}_z\text{Ga}_{1-z}\text{As}$ (where $0 \leq z \leq 1$), and

wherein the first multilayer structure includes semiconductor layers made of $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ (where $0 \leq x \leq 1$ and $0 \leq y \leq 1$).

18. (Currently Amended) A semiconductor laser device comprising:
a buffer layer formed on a compound semiconductor substrate;
an etching control layer, which is formed on a first region of the buffer layer and has a composition different from a composition of the substrate;

a first semiconductor laser structure, which is defined in a first region on the etching control layer and which is made up of a first multiple semiconductor layers including a first active layer with a composition different from that of the etching control layer; and

a second semiconductor laser structure, which is defined ~~in on~~ on a second region ~~on the etching control layer of the buffer layer~~ and which is made up of a second multiple semiconductor layers including a second active layer,

wherein the first multiple semiconductor layers are made of III-V compound, the V element is one selected from the group consisting of As and P,

wherein the second multiple semiconductor layers are made of III-V compound, the V

element is another selected from the group consisting of As and P, and
wherein the etching control layer has a V element different from the V element
comprising of the first multiple semiconductor layers.